# 2SC2590

## Silicon NPN epitaxial planar type

## For low-frequency power amplification

## ■ Features

- $\bullet$  Excellent collector current  $I_C$  characteristics of forward current transfer ratio  $h_{FE}$
- High transition frequency f<sub>T</sub>
- TO-126B package which requires no insulation plate for installation to the heat sink

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	120	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	120	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_{C}$	0.5	A	
Peak collector current	$I_{CP}$	1.0	A	
Collector power dissipation	Pc	1.2	W	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

# 0.75±0.1 Unit: mm 3.2±0.2 0.5±0.1 0.5±0.1 0.5±0.1 1.76±0.1 1.76±0.1 1.76±0.1 0.5±0.1 0

## ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_{\rm C} = 100  \mu \rm A,  I_{\rm B} = 0$	120			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_{\rm E} = 10  \mu \text{A}, I_{\rm C} = 0$	5			V
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = 10 \text{ W}, I_{C} = 150 \text{ mA}$	90		220	_
	h <sub>FE2</sub>	$V_{CH} = 5 \text{ V}, I_{C} = 500 \text{ mA}$	65	100		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$			1.0	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$			1.2	V
Transition frequency	F	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		11	20	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

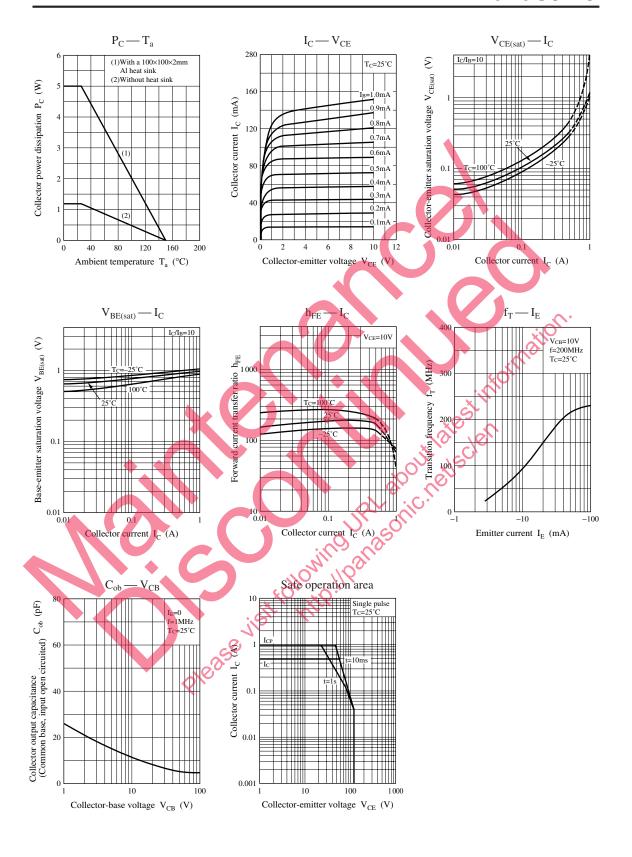
2. \*1: Pulse measurement

### \*2: Rank classification

Rank	Q	R
h <sub>FE1</sub>	90 to 155	130 to 220

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